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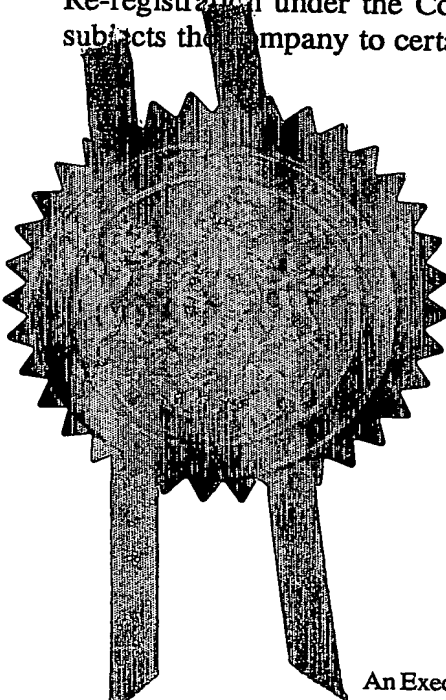
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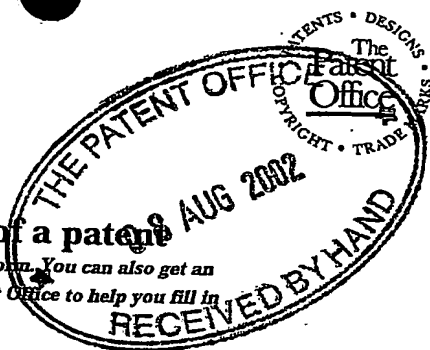
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Research Ventures Group
Third Floor, Senate House
Tyndall Avenue
Bristol BS8 1TH
United Kingdom

Patents ADP number (if you know it)

If the applicant is a corporate body, give the country/state of its incorporation

GB

798181012
04082442005

4. Title of the invention

TUNABLE LASING DEVICE

5. Name of your agent (if you have one)

Haseltine Lake

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Patents ADP number (if you know it)

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Number of earlier application

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Claim(s)

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Abstract

1

Drawing(s)

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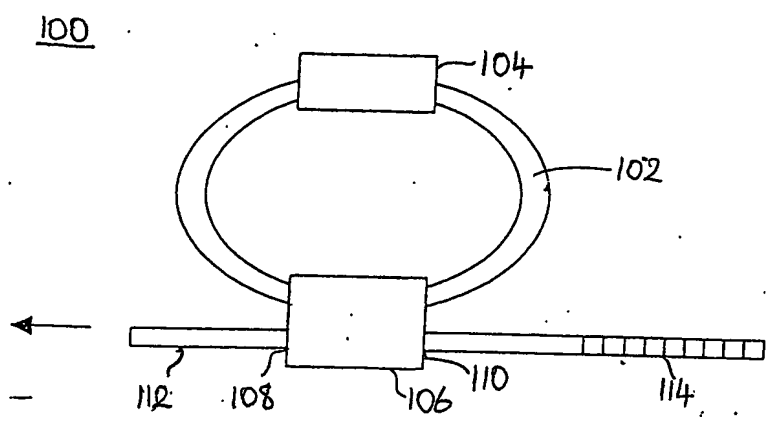


FIG. 1A

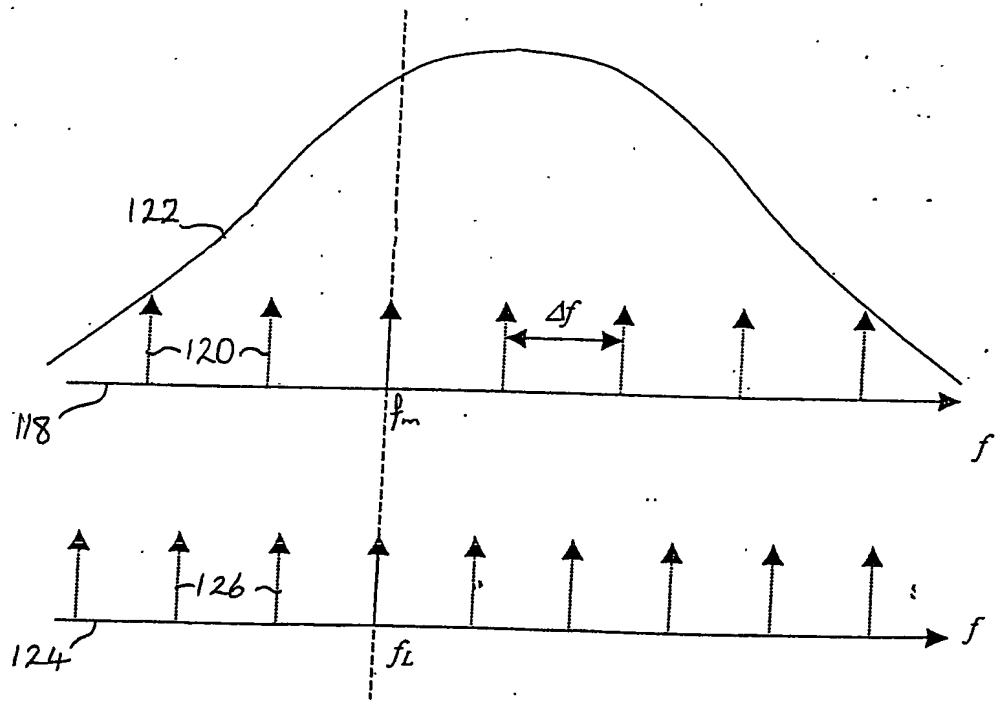
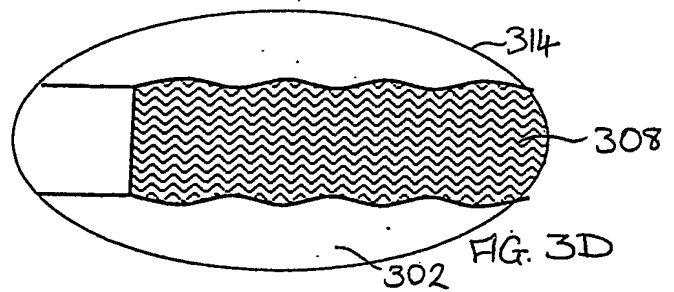
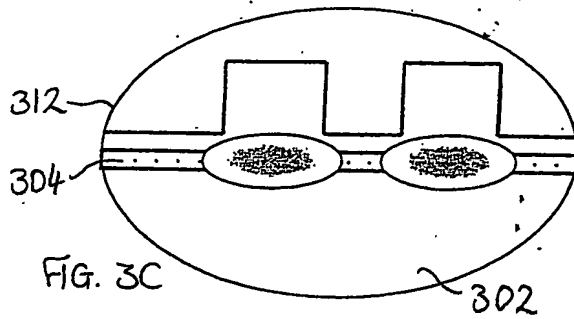
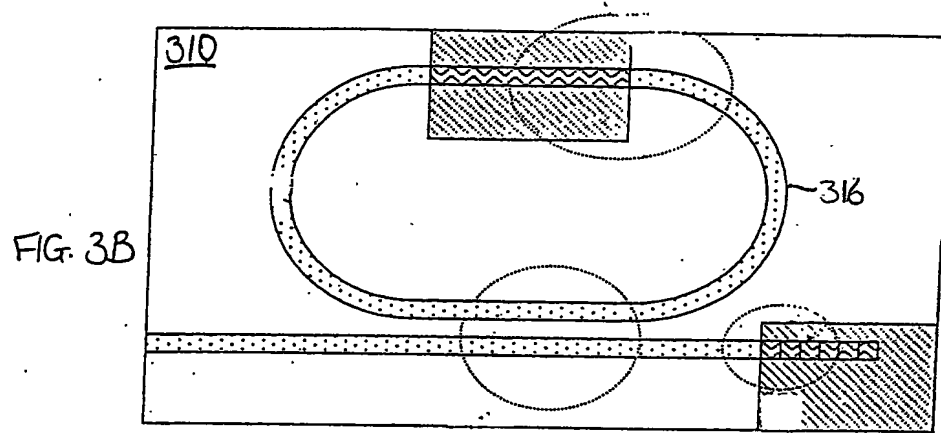
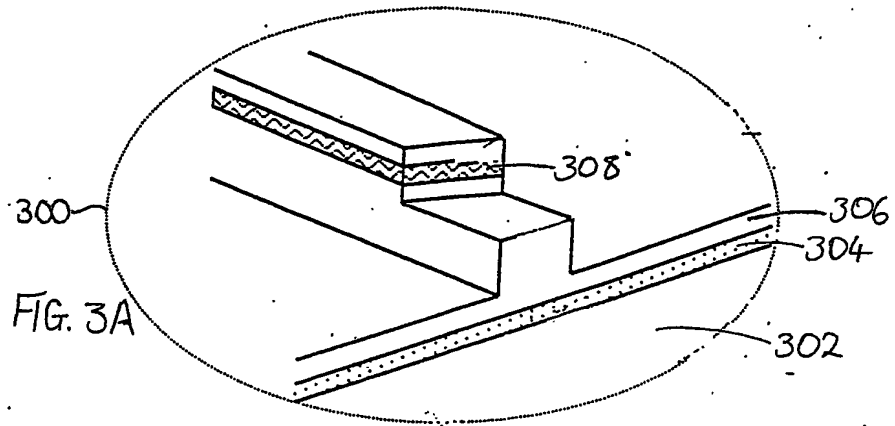


FIG. 1B



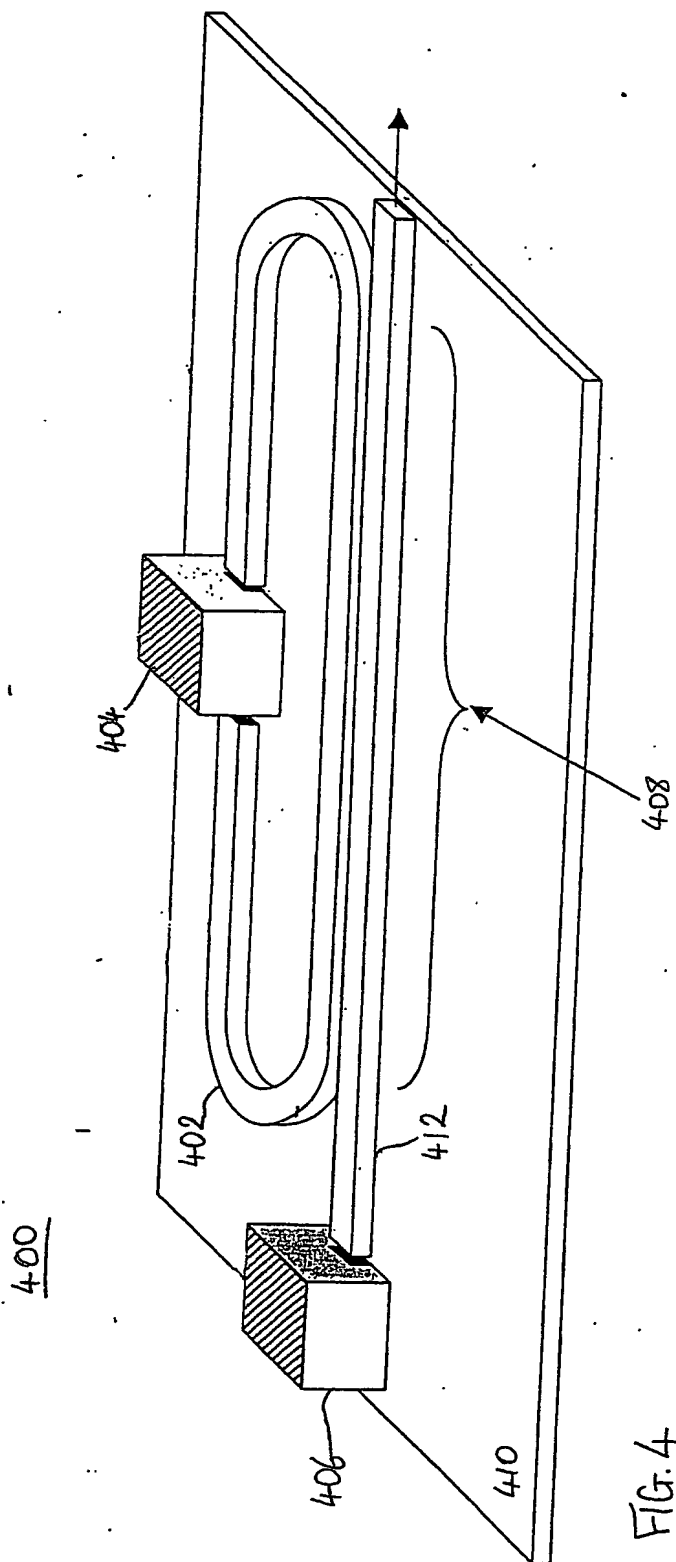


FIG. 4

100

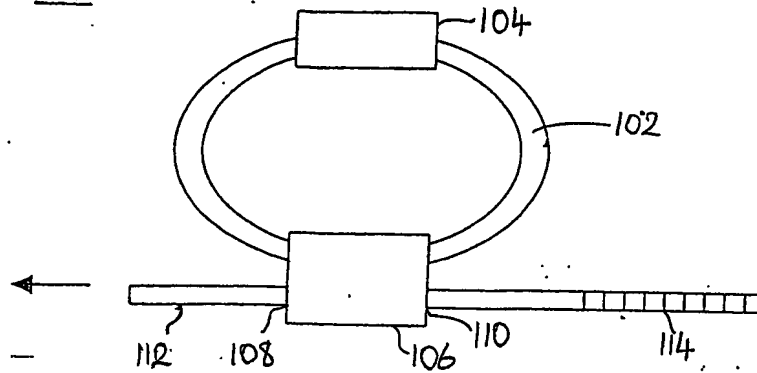


FIG. 1A

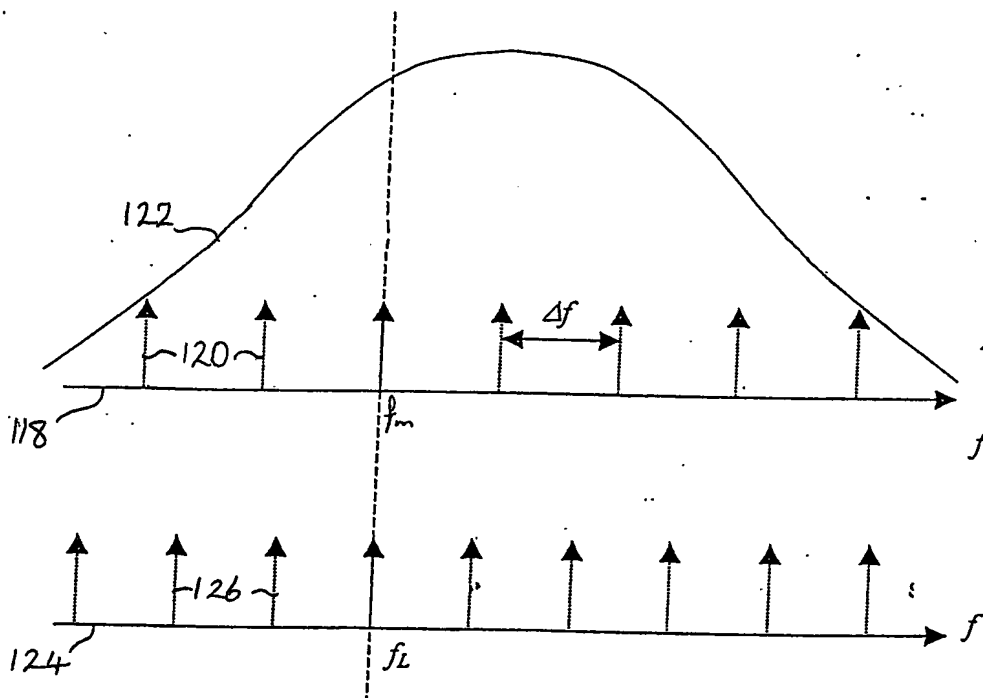


FIG. 1B

FIG. 3A

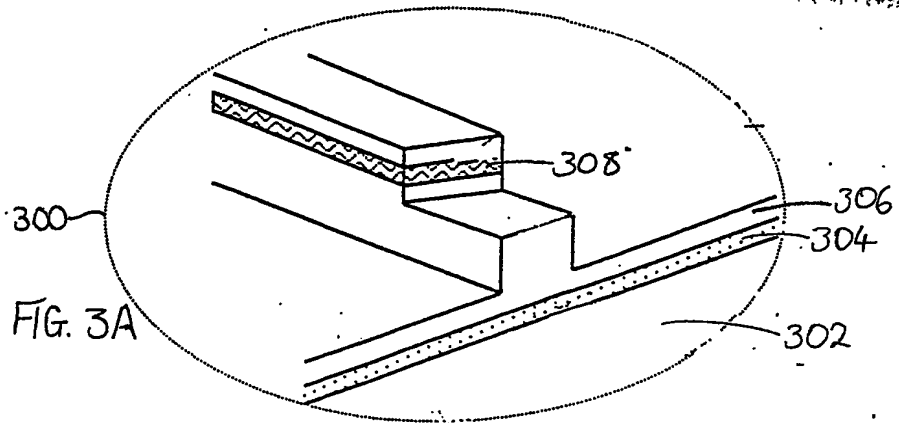


FIG. 3B

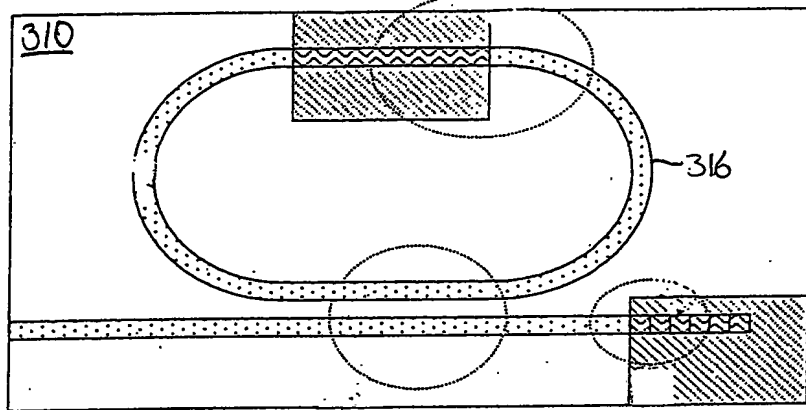


FIG. 3C

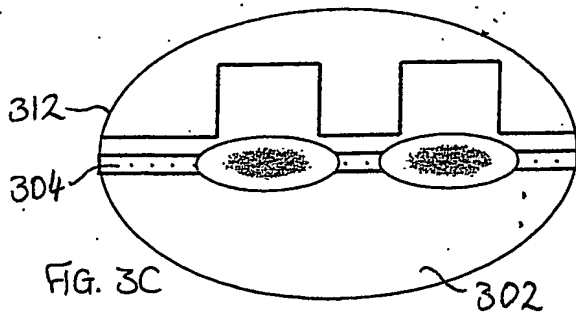
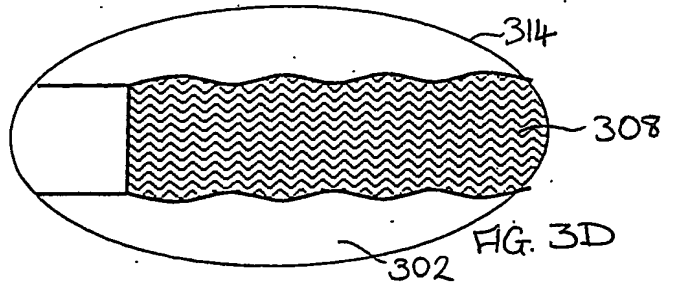


FIG. 3D



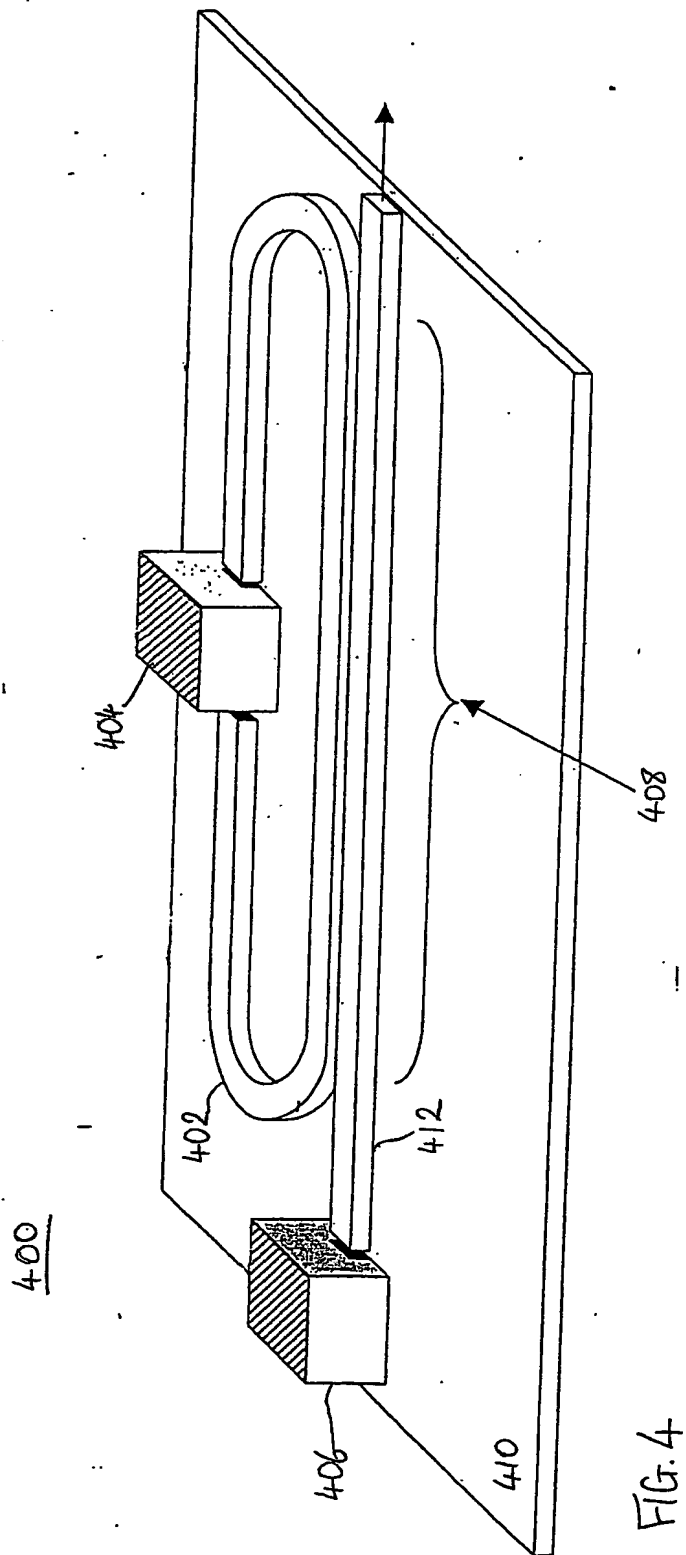


FIG. 4

DUPLICATE

TUNABLE LASING DEVICE

Technical Field of the Invention

The present invention relates to an optoelectronic device, and in particular to a lasing device that can change an emitted wavelength at high speed.

Description of Related Art

Tunable lasers are commonly used as sources in high capacity optical telecommunication systems, such as dense wavelength division multiplexing (DWDM) systems. This technique involves transmitting several optical signals via a single fibre with the optical signals having slightly differing respective wavelengths. A related technique, known as wavelength routing, involves transmitting data using precise wavelengths and rapidly interchanging between those wavelengths. Tunable lasers are also used in photonic switching systems and also find application in other fields, such as spectroscopy and optical sensing.

Conventional tunable semiconductor diode lasers are generally one of three types. The first type is known as a "Y-cavity laser" (see M.J. Kuznetsov, J. of Lightwave Technology, Vol.12, Issue 12, Dec 1994), in which extended tuning (near 40 nm) is achieved by adopting an external interferometer. However, Y-cavity lasers suffer from a limited side mode suppression ratio (SMSR) of less than 25dB.

The second type of conventional tunable laser is known as "grating assisted co-directional coupler (GACC) laser" (see Z.M. Chuang, and L.A. Coldren, IEEE J. of Quantum Electronics, Vol.29 Issue 4, April 1993), which also

suffers from a limited SMSR, due to broadening of a gain-filter bandwidth whilst the laser is tuned.

The third type of conventional tunable laser is known as a "sampled grating distributed reflector (SGDBR) laser" (see L.A. Coldren, IEEE J. of Selected Topics in Quantum Electronics, Vol. 6, Issue 6, Nov-Dec. 2000 and references therein; F. Delorme, IEEE J. of Quantum Electronics, Vol.34 Issue 9, Sep. 1998). In order to set an operating wavelength for SGDBR lasers it is necessary to determine at least three control variables. Each control variable is an external current source with a value determined from a multi-dimensional look-up table (which must be pre-programmed in a time consuming 'training' process). The process of determining the control variables involves processing in several different zones in the multi-dimensional variable space. The slow speed of this processing leads to an inadequate tuning speed for efficient operation of, for example, optical packet transmission systems. This problem is further compounded by transient phenomena in the laser cavity which have relatively long decay times (such as thermal stabilizing time for the grating). SGDBR lasers generally include phase matching components which add complexity and increase the dimensions of the device.

Therefore, the present invention seeks to provide a tunable laser in which the problems of conventional tunable lasers are at least alleviated.

Summary

According to an aspect of the present invention, there is provided a lasing device comprising a ring cavity and a frequency selection means, wherein the frequency

selection means comprises a control means for controlling a refractive index of the frequency selection means.

Further, the frequency selection means is operable to supply a feedback signal to the ring cavity laser, and to select the frequency of the feedback signal.

The tunable lasing device as described above can be utilised in an optical communication system.

Advantageously, the tunable laser of the present invention emits precise, discrete wavelengths as determined by the cavity modes of the laser cavity. These modes are determined during laser manufacture and can be precisely trimmed to the accurate values required.

Further advantage is gained in that the wavelength tuning occurs at a high speed (in the order of nanoseconds). Primarily, four factors contribute to achieving this high speed tuning. Firstly, a wavelength selection means which operates at a high speed is used. Secondly, a wavelength lock-in time of the present invention is shorter than that of conventional tunable lasers. Wavelength lock-in time refers to the time for an output wavelength to stabilize to a predetermined value. Thirdly, only a single control variable needs to be determined in order to set an operating wavelength for the tunable laser. Fourthly, after the initial wavelength lock-in time, the emitted wavelength is no longer affected by possible long-term transience (such as thermal drift) In this way, the time required for the tunable laser to change between different emitted wavelengths is minimized and also, phase matching components (as required in some SGDBR lasers) are not necessary.

Brief Description of the Drawings

For a better understanding of the present invention, and to show how it may be put into effect, reference will now be made, by way of example, to the accompanying drawings in which:

Figure 1A is a schematic diagram of a tunable laser in accordance with an embodiment of the present invention;

Figure 1B shows a graph illustrating single mode laser operation of the tunable laser of Figure 1A;

Figure 2A illustrates an enlarged cross-section of an optical gain element of a first implementation of the present invention;

Figure 2B illustrates a plan view of a ring cavity laser of a first implementation of the present invention;

Figure 2C illustrates an enlarged cross-section of a grating element of a first implementation of the present invention;

Figure 3A illustrates an enlarged cross-section of an optical gain element of a second implementation of the present invention;

Figure 3B illustrates a plan view of a ring cavity laser of a second implementation of the present invention;

Figure 3C illustrates an enlarged cross-section of a grating element of a second implementation of the present invention; and

Figure 4 illustrates a ring cavity laser of a third implementation of the present invention.

Detailed Description of Preferred Embodiment

In the tunable laser 100 of Figure 1A, a ring cavity 102 (comprised of a passive optical waveguide) and an optical gain element 104 are connected to a bi-directional optical output coupler 106. The optical output coupler

106 has a first port 108 and a second port 110. The first port 108 is coupled to an output optical fibre 112 and a second port 110 is coupled to a frequency selection means 114 (such as a grating).

In operation, the optical gain element 104 provides optical gain within a predetermined spectral range and the ring cavity 102 provides a propagation route for circulating photons at one or more wavelengths within the predetermined spectral range. A laser oscillation in the ring cavity 102 occurs at a laser wavelength within the gain spectral range when two operating conditions are met. First, the total optical gain at that laser wavelength f_L exceeds the total optical loss in the ring cavity 102, and second, the optical phase delay associated with a round trip of a photon within the ring cavity 102 is a multiple of 360 degrees.

The graph of Figure 1B illustrates single mode operation of the ring cavity tunable laser 100. The upper section 118 plots the cavity mode frequencies 120 of the ring cavity 102 and shows the laser gain profile 122, and the lower section 124 plots the reflection frequencies 126 of the frequency selection means 114. Where one of the cavity mode frequencies 120 coincides with one of the grating reflection frequencies 126 single mode laser operation is achieved at frequency f_L .

The gain spectral range of the optical gain element 104 (for example, comprising a semiconductor gain medium) usually has a large bandwidth and therefore allows multiple optical frequencies to oscillate at the same time. The cavity mode frequencies 120, f_m , of the ring cavity 102 are primarily determined by the following relationship;

$$f_m = \frac{mc}{nL}$$

where n is the effective refractive index of the ring cavity 102, L is the circumference of the ring cavity 102, (in combination nL is the ring cavity optical path length), m is an integer, and c is the speed of light in a vacuum. The ring cavity mode frequency interval Δf is given by;

$$\Delta f = \frac{c}{nL}.$$

Clearly, varying the circumference of the ring cavity 102 results in altered ring cavity modes 120. Where a frequency selection means 114 has multiple reflecting frequencies 126 (as illustrated in the lower half of Fig.1B), rather than a single reflecting frequency, it is necessary that the reflection frequency intervals of the frequency selection means 114 differ from the ring cavity mode frequency intervals Δf .

Laser emission is initiated by the injection of an electric current into the optical gain element 104. The photon population is increased as the photons pass through the optical gain element 104 until the population gain exceeds the population loss within the ring cavity. Laser output is obtained when the photons exit the ring cavity via the bi-directional output coupler 106.

High speed tuning between single mode laser operation at a first and a second cavity mode frequency is achieved in the following way. A first refractive index of the frequency selection means 114, and therefore a first set of reflection frequencies of the frequency selection means 114, is determined by injecting a first current into the frequency selection means 114. Where one of the first set of reflection frequencies of the frequency

selection means 114 is the same as a cavity mode frequency, lasing occurs at this first cavity mode frequency. Next, a second current is injected into the frequency selection means 114, thus determining a second refractive index of the frequency selection means 114, and therefore a second set of reflection frequencies of the frequency selection means 114. Where one of the second set of reflection frequencies of the frequency selection means 114 is the same as a cavity mode frequency, lasing occurs at this second cavity mode frequency.

The alteration of the current injected into the frequency selection means 114 can change the effective refractive index of the frequency selection means 114, and therefore the reflection frequencies of the frequency selection means 114 in approximately 1 nanosecond. During this tuning process photons are fed back into the ring cavity 102 from the frequency selection means 114.

In the high speed tuning process it is also possible to start lasing at the second cavity mode frequency, instead of the first cavity mode frequency, whilst utilising the first current. This can be achieved by rapidly turning the first current on and off (at, for example, 1 nanosecond intervals).

The optical gain element 200 illustrated in Figure 2A is comprised of a substrate base 202 (such as an III-V semiconductor wafer) onto which an optically active layer 204 is deposited. Further, a semi-insulating semiconductor layer 206, an upper cladding layer 208, a contact layer 210 and finally, ohmic contacts 212 form the upper part of the optical gain element 200.

Figure 2B shows a complete ring cavity laser 214 including the optical gain element 200 of Figure 2A and a grating element 216 of Figure 2C, all of the first implementation. The fabrication process of the ring cavity laser 214 is now described.

In a first epitaxial growth step, an optically active layer 204 that provides optical gain is deposited on the substrate 202. The substrate 202 consists of multiple layers of InGaAsP quaternary compound semiconductor deposited on an Indium Phosphide (InP) substrate. In the area where the grating element 216 is to be fabricated, the surface is patterned by a photolithography or an electron beam lithography process, followed by an etching process, to form grating corrugations 218. The optically active layer 204 is then removed from the substrate 202 except for areas where the optical gain element 200 and the grating element 216 are to be fabricated.

In a second growth step, an optically passive layer 220 is deposited on the substrate 202 in areas where the optically active layer 204 has been removed. The position of this optically passive layer 220 is vertically aligned to that of the optically active layer 204 (and the thickness of both layers are comparable). The ring cavity laser 214 is then completed by a photolithography process that defines ridge waveguides which form the ring cavity 222, the output coupler 224 and the grating element 216. The entire structure is buried in the semi-insulating semiconductor layer 206 (except for the top of the waveguides) and the upper cladding layer 208 and the contact layer 210 are grown on top. The ohmic contacts 212 are then formed on the optical gain element 200 and the grating 216.

The grating element 216 illustrated in Figure 2C is generally a sampled grating reflector formed in a similar way to the optical gain element 200 of Figure 2A.

The lasing and tuning operations of the first implementation of the ring cavity laser 214 (shown in Figures 2A, 2B and 2C) are as described for the embodiment of the invention in Figures 1A and 1B and will not be repeated here for the sake of brevity.

The optical gain element 300 of the second implementation illustrated in Figure 3A is comprised of a substrate base 302 onto which an optically passive layer 304 is deposited. A spacer layer 306 and an optically active layer 308 form the upper part of the optical gain element 300. The optically active layer 308 forms active vertical couplers with the optically passive layer 304 underneath (thereby creating a photonic integrated circuit (PIC)).

Figure 3B shows a complete ring cavity laser 310 including the optical gain element 300 of Figure 3A, the output coupler 312 of Figure 3C and the grating element 314 of Figure 3D, all of a second implementation. Each feature is monolithically integrated onto the substrate 302. The fabrication process of the ring cavity laser 310 is mainly as described for the first implementation of the invention in Figures 2A to 2C, with the following exceptions.

The ring cavity waveguide 316 and the output coupler 312 are formed in the optically passive layer 304. In order to achieve this, the optically active layer 308 is removed from the substrate 302 in these areas. The grating element 314, like the gain element 300, is formed in the optically active layer 308. During fabrication

the width of the waveguide, in the area designated for the grating element 314, is periodically varied. Alternatively, the grating element 314 can be formed by the etching corrugations in the waveguide.

The lasing and tuning operations of the second implementation of the ring cavity laser 310 (shown in Figures 3A, 3B 3C and 3D) are as described for the embodiment of the invention in Figures 1A and 1B and will not be repeated here for the sake of brevity.

Figure 4 shows a complete ring cavity laser 400 of a third implementation. A ring cavity waveguide 402, an optical gain element 404, a grating element 406 and an output coupler 408 are hybrid integrated onto a planar substrate 410. The fabrication process of the ring cavity laser 400 involves deposition of several optically passive layers (not specifically illustrated) onto the substrate 410 which are used to form the ring cavity waveguide 402 and the output coupler 408.

The optical gain element 404 is a semiconductor optical amplifier which is positioned in a gap where the ring cavity waveguide 402 has been removed for that purpose. The length of the gap is suitable for efficient butt-coupling of light into and out of the semiconductor optical amplifier 404. The grating element 406 is separately fabricated in a waveguide material and butt-coupled to one of the output waveguides 412 of the ring cavity laser 400.

Preferably, reflection at the butt-coupled joints is minimized. In order to achieve this, it may be necessary to utilize a non-perpendicular angle between the end-facets of the gain element 404 or grating element 406 and

the waveguides 402 412. Other anti-reflection means, such as optical coatings can also be employed.

The lasing and tuning operations of the third implementation of the ring cavity laser 400 (shown in Figure 4) are as described for the embodiment of the invention in Figures 1A and 1B and will not be repeated here for the sake of brevity.

It will be apparent to the skilled person that the above described implementations of the invention are not exhaustive and variations on these structures may be employed to achieve a similar result whilst employing the same inventive concept. Individual elements within each implementation can be replaced with any element or combination of elements which performs a similar function. For example, the grating element may be replaced with any suitable multi-frequency band filter. Further, the positions of the optically passive layer and the optically active layer may be interchangeable in some implementations (similar to the second implementation of the present invention). Consequently the fabrication process would need to be adapted.

It can therefore be seen that the present invention provides a tunable lasing device which has significant advantages over conventional devices.

CLAIMS:

1. A lasing device comprising a ring cavity and a frequency selection means, wherein the frequency selection means comprises:
a control means for controlling a refractive index of the frequency selection means.
2. A lasing device as claimed in claim 1, wherein the control means is a variable current source.
3. A lasing device as claimed in claims 1 and 2, wherein lasing occurs when a resonant frequency of the ring cavity is substantially the same as the reflection frequency of the frequency selection means.
4. A lasing device comprising a ring cavity laser coupled to a frequency selection means, the frequency selection means being operable to supply a feedback signal to the ring cavity laser, and to select the frequency of the feedback signal.
5. The lasing device as claimed in any preceding claim, wherein the frequency selection means is a grating.
6. The lasing device as claimed in any of claims 1 or 4, further comprising:
an optical gain element, and
an output coupler.
7. The lasing device as claimed in claim 6, wherein the output coupler is a bi-directional coupler.
8. The lasing device as claimed in claim 7, wherein the frequency selection means and the optical gain element are comprised of an optically passive layer and an

optically active layer, a semi-insulating layer, an upper cladding layer and an ohmic contact layer; and

the frequency selection means further comprising corrugations formed by an etching process.

9. The lasing device as claimed in claim 7, wherein the optical gain element, the grating, the output coupler and the ring cavity are monolithically integrated onto a substrate;

the optical gain element is comprised of an optically passive layer and an optically active layer separated by a spacer layer;

the grating is comprised of a waveguide made from an optically passive layer and an optically active layer; and

the output coupler and the ring cavity are formed in an optically passive layer.

10. The lasing device as claimed in claim 9, wherein the grating is formed by periodically varying the width of the waveguide.

11. The lasing device as claimed in claim 9, wherein the grating is formed by etching corrugations in the waveguide.

12. The lasing device as claimed in claim 7, wherein the optical gain element, the grating, the output coupler and the ring cavity are hybrid integrated onto a substrate; and

the optical gain element and the grating are butt-coupled to the ring cavity.

13. An optical communication system including a tunable lasing device as claimed in any preceding claim.

Abstract**Tunable lasing device**

A tunable lasing device comprising a ring-shaped laser cavity, an optical gain element, a bi-directional output coupler and a frequency selection means. The frequency selection means is generally a grating with a refractive index that determines a grating reflection frequency. Single mode laser operation is achieved where a cavity mode frequency of the ring-shaped laser cavity coincides with a grating reflection frequency. The refractive index of the grating can be modified by the injection of a variable current. In this way, the lasing frequency can be rapidly tuned between cavity mode frequencies.

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